

	Type	Hits	Search Text	DBs
20	BRS	18	S18 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
21	BRS	199750 5	display	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
22	BRS	312545	pixel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
23	BRS	78690	tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
24	BRS	75073	phase-change or (phase near change)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
25	BRS	175725 2	memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
26	BRS	224193	nonvolatile or non-volatile	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
27	BRS	4308	S24 same S25	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT

	Type	Hits	Search Text	DBs
28	BRS	617	S27 same S26	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
29	BRS	16	S28 and S22 and S21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
30	BRS	45	chalconide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
31	BRS	14406	chalcogen\$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
32	BRS	29288	S21 and S22 and S23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
33	BRS	238620 1	storage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
34	BRS	4308	S24 same S25	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
35	BRS	603	S38 same S34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT

	Type	Hits	Search Text	DBs
36	BRS	18	S39 and S23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
37	BRS	1	S40 and S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
38	BRS	2	S29 and S23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
39	BRS	51	"4432610"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
40	BRS	16	S28 and S22 and S21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
41	BRS	71	S34 and S35	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
42	BRS	18	S39 and S23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
43	BRS	8	S23 same S34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT

	Type	Hits	Search Text	DBs
44	BRS	3920	S25 same S23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
45	BRS	2889	S44 and S21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
46	BRS	2	S45 and S32	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
47	BRS	1999	S45 and S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
48	BRS	3	S47 and S34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
49	BRS	70235	variable near resistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
50	BRS	14859	varistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
51	BRS	84286	S49 or S50	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT

	Type	Hits	Search Text	DBs
52	BRS	65742	thin near film near transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
53	BRS	105651	S23 or S52	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
54	BRS	275	S51 same S53	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
55	BRS	180941	S21 and S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
56	BRS	194	S54 and S55	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
57	BRS	37	S56 and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
58	BRS	238620 1	storage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
59	BRS	64	S56 and S58	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT

	Type	Hits	Search Text	DBs
60	BRS	1805	S53 and (S24 or S26 or S34) and S21 and S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
61	BRS	5	S54 and S34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
62	BRS	42010	variable near resistance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
63	BRS	44	S62 same S53	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
64	BRS	1736	S53 and (S24 or S26) and S21 and S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
65	BRS	13	S64 and S34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
66	BRS	15561	S21 and S22 and (S24 or S26)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
67	BRS	81	S22 same (S24 or S26) same S53	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT

	Type	Hits	Search Text	DBs
68	BRS	114577	S62 or S51	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
69	BRS	2	S67 and S68	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
70	BRS	339	S68 same S26 same S25	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
71	BRS	1	S70 same S53	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
72	BRS	10	S70 and S53	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
73	BRS	105	S68 and S26 and S25 and S53	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
74	BRS	304	S68 same S53	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT
75	BRS	3	S73 and S74	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT